Anton Gutakovskii

List of Publications by Year
in descending order

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230	2,215	331259	395343
papers	citations	21 h-index	33 g-index

231	231	231	1971
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Normal-incidence infrared photoconductivity in Si p-i-n diode with embedded Ge self-assembled quantum dots. Applied Physics Letters, 1999, 75, 1413-1415.	1.5	108
2	Magnetic field-induced dissipation-free state in superconducting nanostructures. Nature Communications, 2013, 4, 1437.	5.8	90
3	Synthesis and Characterization of Cu_xS (x = 1â€“2) Nanocrystals Formed by the Langmuirâ€“Blodgett Technique. Journal of Physical Chemistry C, 2014, 118, 23409-23414.	1.5	57
4	Closed curved graphite-like structures formation on micron-size diamond. Chemical Physics Letters, 1998, 289, 353-360.	1.2	56
5	Atomic and energy structure of InAs/AlAs quantum dots. Physical Review B, 2008, 78, .	1.1	52
6	Effect of Quantum Confinement on Optical Properties of Ge Nanocrystals in GeO[sub 2] Films. Semiconductors, 2005, 39, 1168.	0.2	51
7	Exciton recombination dynamics in an ensemble of (In,Al)As/AlAs quantum dots with indirect band-gap and type-I band alignment. Physical Review B, 2011, 84, .	1.1	42
8	Application of high-resolution electron microscopy for visualization and quantitative analysis of strain fields in heterostructures. Bulletin of the Russian Academy of Sciences: Physics, 2007, 71, 1426-1432.	0.1	38
9	Apoptosis-mediated endothelial toxicity but not direct calcification or functional changes in anti-calcification proteins defines pathogenic effects of calcium phosphate bions. Scientific Reports, 2016, 6, 27255.	1.6	37
10	Properties of extremely thin silicon layer in silicon-on-insulator structure formed by smart-cut technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 82-86.	1.7	35
11	GeSi films with reduced dislocation density grown by molecular-beam epitaxy on compliant substrates based on porous silicon. Applied Physics Letters, 1999, 75, 4118-4120.	1.5	28
12	High quality relaxed GaAs quantum dots in GaP matrix. Applied Physics Letters, 2010, 97, 023108.	1.5	27
13	Charge Berezinskii-Kosterlitz-Thouless transition in superconducting NbTiN films. Scientific Reports, 2018, 8, 4082.	1.6	27
14	Fluorinated graphene suspension for flexible and printed electronics: Flakes, 2D films, and heterostructures. Materials and Design, 2019, 164, 107526.	3.3	27
15	Ge/Si quantum dot nanostructures grown with low-energy ion beam-assisted epitaxy. Surface and Coatings Technology, 2005, 196, 25-29.	2.2	25
16	Atomic structure and energy spectrum of Ga(As,P)/GaP heterostructures. Journal of Applied Physics, 2012, 112, .	1.1	25
17	Enhancement of the Si p-n diode NIR photoresponse by embedding Î²-FeSi2 nanocrystallites. Scientific Reports, 2015, 5, 14795.	1.6	24
18	Mechanisms of edge-dislocation formation in strained films of zinc blende and diamond cubic semiconductors epitaxially grown on (001)-oriented substrates. Journal of Applied Physics, 2011, 109, .	1.1	23

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19	Mechanism of induced nucleation of misfit dislocations in the Ge-on-Si(0 0 1) system and its role in the formation of the core structure of edge misfit dislocations. Acta Materialia, 2013, 61, 617-621.	3.8	23
20	LiVPO4F/Li3V2(PO4)3 nanostructured composite cathode materials prepared via mechanochemical way. Journal of Solid State Electrochemistry, 2014, 18, 1389-1399.	1.2	23
21	High resolution electron microscopy of semiconductor interfaces. Physica Status Solidi A, 1995, 150, 127-140.	1.7	22
22	Surface-enhanced Raman spectroscopy of semiconductor nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 75, 210-222.	1.3	22
23	Direct observations of dislocation half-loops inserted from the surface of the GeSi heteroepitaxial film. Applied Physics Letters, 2004, 85, 6140-6142.	1.5	21
24	Solid solutions GeSi grown by MBE on a low temperature Si (001) buffer layer: specific features of plastic relaxation. Thin Solid Films, 2001, 392, 98-106.	0.8	20
25	Plastic relaxation of solid GeSi solutions grown by molecular-beam epitaxy on the low temperature Si(100) buffer layer. Journal of Applied Physics, 2002, 91, 4710-4714.	1.1	20
26	Linear chains of Ge/Si quantum dots grown on a prepatterned surface formed by ion irradiation. Semiconductors, 2015, 49, 749-752.	0.2	20
27	Strain relaxation of GeSi/Si(001) heterostructures grown by low-temperature molecular-beam epitaxy. Journal of Applied Physics, 2004, 96, 7665-7674.	1.1	19
28	Potentialities and basic principles of controlling the plastic relaxation of GeSi/Si and Ge/Si films with stepwise variation in the composition. Semiconductors, 2008, 42, 1-20.	0.2	19
29	Features of formation and propagation of 60Â° and 90Â° misfit dislocations in GexSi1âˆ’xâˆ•Siâ€ˆ(xâ‰¤0.4â€“0.5) films caused by Si substrate misorientation from (001). Applied Physics Letters, 2008, 92, .	1.5	19
30	Pseudomorphic GeSiSn, SiSn and Ge layers in strained heterostructures. Nanotechnology, 2018, 29, 154002.	1.3	19
31	Atomic and electronic structure of ferroelectric La-doped HfO₂ films. Materials Research Express, 2019, 6, 036403.	0.8	19
32	Heterostructures GexSi1âˆ’x/Si(001) (x=0.18â€“0.62) grown by molecular beam epitaxy at a low (350 Â°C) temperature: specific features of plastic relaxation. Thin Solid Films, 2004, 466, 69-74.	0.8	18
33	Strong sensitivity of photoluminescence of InAs/AlAs quantum dots to defects: evidence for lateral inter-dot transport. Semiconductor Science and Technology, 2006, 21, 527-531.	1.0	18
34	Optically detected magnetic resonance of photoexcited electrons in (In,Al)As/AlAs quantum dots with indirect band gap and type-I band alignment. Physical Review B, 2018, 97, .	1.1	18
35	The influence of irradiation and subsequent annealing on Si nanocrystals formed in SiO2 layers. Semiconductors, 2000, 34, 965-970.	0.2	17
36	Precise surface measurements at the nanoscale. Measurement Science and Technology, 2010, 21, 054004.	1.4	17

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37	Initial stage growth of Ge x Si1â^'x layers and Ge quantum dot formation on Ge x Si1â^'x surface by MBE. Nanoscale Research Letters, 2012, 7, 561.	3.1	17
38	Different electrochemical responses of LiFe0.5Mn0.5PO4 prepared by mechanochemical and solvothermal methods. Journal of Alloys and Compounds, 2018, 742, 454-465.	2.8	17
39	A new approach to the fabrication of VO₂ nanoswitches with ultra-low energy consumption. Nanoscale, 2020, 12, 3443-3454.	2.8	17
40	Optical vibration modes in (Cd, Pb, Zn)S quantum dots in the Langmuir-Blodgett matrix. Physics of the Solid State, 2002, 44, 1976-1980.	0.2	16
41	Preparation of thin films of platinum group metals by pulsed MOCVD. I. Deposition of Ir layers. Journal of Structural Chemistry, 2012, 53, 715-724.	0.3	16
42	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. Applied Physics Letters, 2015, 107, .	1.5	16
43	Quantum dots formed in InSb/AlAs and AlSb/AlAs heterostructures. JETP Letters, 2016, 103, 692-698.	0.4	16
44	Probing the Mg2Si/Si(1 1 1) heterojunction for photovoltaic applications. Solar Energy, 2020, 211, 383-395.	2.9	16
45	The formation of partial misfit dislocations during heteroepitaxy. Physica Status Solidi A, 1981, 67, 299-304.	1.7	15
46	Formation of edge misfit dislocations in GexSi1â^'x (xâ^¼0.4â€“0.5) films grown on misoriented (001)â†'(111) Si substrates. Journal of Crystal Growth, 2008, 310, 3422-3427.	0.7	15
47	Hemozoin â€œknobsâ€•in Opisthorchis felineus infected liver. Parasites and Vectors, 2015, 8, 459.	1.0	15
48	The convenient preparation of stable aryl-coated zerovalent iron nanoparticles. Beilstein Journal of Nanotechnology, 2015, 6, 1192-1198.	1.5	15
49	Novel self-assembled quantum dots in the GaSb/AlAs heterosystem. JETP Letters, 2012, 95, 534-536.	0.4	14
50	The Mechanism of {113} Defect Formation in Silicon: Clustering of Interstitialâ€“Vacancy Pairs Studied by In Situ High-Resolution Electron Microscope Irradiation. Microscopy and Microanalysis, 2013, 19, 38-42.	0.2	14
51	Heterostructures with diffused interfaces: Luminescent technique for ascertainment of band alignment type. Journal of Applied Physics, 2018, 123, 115701.	1.1	14
52	On the structure and photoluminescence of dislocations in silicon. Journal of Applied Physics, 2018, 124, 053106.	1.1	14
53	Study of Onion-Like Carbon (OLC) Formation from Ultra Disperse Diamond (UDD). Materials Research Society Symposia Proceedings, 1994, 359, 105.	0.1	13
54	Effect of ion dose and annealing mode on photoluminescence from SiO2 implanted with Si ions. Semiconductors, 1998, 32, 1222-1228.	0.2	13

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55	Growth and structure of Ge nanoislands on an atomically clean silicon oxide surface. Physics of the Solid State, 2004, 46, 77-79.	0.2	13
56	Interface phonons in semiconductor nanostructures with quantum dots. Journal of Experimental and Theoretical Physics, 2005, 101, 554-561.	0.2	13
57	Sb as surfactant at plastic relaxation of GeSi/Si(001) films grown by molecular-beam epitaxy: Reduction of surface roughness value. Journal of Crystal Growth, 2006, 297, 57-60.	0.7	13
58	Pulsed ion-beam induced nucleation and growth of Ge nanocrystals on SiO2. Applied Physics Letters, 2007, 90, 133120.	1.5	13
59	Growth, structure and luminescence properties of multilayer Si/Î²-FeSi2NCs/Si/â€¦/Si nanoheterostructures. Thin Solid Films, 2011, 519, 8480-8484.	0.8	13
60	CdZnS quantum dots formed by the Langmuirâ€“Blodgett technique. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 04D109.	0.6	13
61	A room-temperature-operated Si LED with Î²-FeSi2 nanocrystals in the active layer: Î¼W emission power at 1.5â€‰Î¼m. Journal of Applied Physics, 2017, 121, .	1.1	13
62	Heterostructures GexSi1âˆ’x/Si(001) grown by low-temperature (300â€“400Â°C) molecular beam epitaxy: Misfit dislocation propagation. Journal of Crystal Growth, 2005, 280, 309-319.	0.7	12
63	The formation of silicon nanocrystals in SiO2 layers by the implantation of Si ions with intermediate heat treatments. Semiconductors, 2005, 39, 552-556.	0.2	12
64	Nonradiative energy transfer between vertically coupled indirect and direct bandgap InAs quantum dots. Applied Physics Letters, 2010, 97, 263102.	1.5	12
65	Crystallization of Amorphous Si Nanoclusters in SiO_x Films Using Femtosecond Laser Pulse Annealings. Journal of Nanoscience and Nanotechnology, 2012, 12, 8694-8699.	0.9	12
66	Oxide-free InAs(111)A interface in metal-oxide-semiconductor structure with very low density of states prepared by anodic oxidation. Applied Physics Letters, 2014, 105, .	1.5	12
67	Influence of the additional p⁺â€‰doped layers on the properties of AlGaAs/InGaAs/AlGaAs heterostructures for high power SHF transistors. Journal Physics D: Applied Physics, 2016, 49, 095108.	1.3	12
68	Splitting and electrical properties of the SOI structure formed from the heavily boron doped silicon with using of the smart-cut technology. Microelectronic Engineering, 1999, 48, 383-386.	1.1	11
69	Specific features of formation and propagation of 60Â° and 90Â° misfit dislocations in GexSi1âˆ’x/Si films with x>0.4. Journal of Crystal Growth, 2010, 312, 3080-3084.	0.7	11
70	Initial stages of Ge epitaxy on Si(111) under quasi-equilibrium growth conditions. JETP Letters, 2010, 92, 388-395.	0.4	11
71	Evolution of silicon nanoclusters and hydrogen in SiNx:H films: Influence of high hydrostatic pressure under annealing. Thin Solid Films, 2012, 520, 6207-6214.	0.8	11
72	Dislocation interaction of layers in the Ge/Ge-seed/Ge Si1âˆ’x/Si(0 0 1) (xâ‰¤ 0.3â€“0.5) system: Trapping of misfit dislocations on the Ge-seed/GeSi interface. Acta Materialia, 2013, 61, 5400-5405.	3.8	11

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73	Dominating nucleation of misfit dislocations from the surface in GeSi/Si(001) films with a stepwise composition grown by means of molecular-beam epitaxy. Journal of Crystal Growth, 2006, 293, 247-252.	0.7	10
74	Formation of edge misfit dislocations in GexSi1âˆ’x(xâ‰¼0.4â€“0.8) films grown on misoriented (001)â†’(111) Si substrates: Features before and after film annealing. Journal of Applied Physics, 2010, 107, .	1.1	10
75	Formation of a Thin Continuous GaSb Film on Si(001) by Solid Phase Epitaxy. Nanomaterials, 2018, 8, 987.	1.9	10
76	Aluminum-induced crystallization of silicon suboxide thin films. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	1.1	10
77	Effect of the structure and the phase composition on the mechanical properties of Alâ€“Cuâ€“Li alloy laser welds. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2021, 809, 140947.	2.6	10
78	Study of InGaAsï£¿GaAs strained-layer superlattices by TEM and RBS techniques. Physica Status Solidi A, 1989, 115, 413-425.	1.7	9
79	Electrical conductivity of silicon-on-insulator structures prepared by bonding silicon wafers to a substrate using hydrogen implantation. Semiconductors, 2000, 34, 1054-1057.	0.2	9
80	Enhanced strain relaxation in a two-step process of GexSi1âˆ’x/Si(001) heterostructures grown by low-temperature molecular-beam epitaxy. Applied Physics Letters, 2004, 84, 4599-4601.	1.5	9
81	Defects in the crystal structure of Cd x Hg1 âˆ’ x Te layers grown on the Si (310) substrates. Semiconductors, 2011, 45, 926-934.	0.2	9
82	Resonant plasmon enhancement of light emission from CdSe/CdS nanoplatelets on Au nanodisk arrays. Journal of Chemical Physics, 2020, 153, 164708.	1.2	9
83	Electron-nuclei interaction in the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>X</mml:mi></mml:math> valley of (In,Al)As/AlAs quantum dots. Physical Review B, 2020, 101, .	1.1	9
84	Robust semiconductor-on-ferroelectric structures with hafniaâ€“zirconiaâ€“alumina UTBOX stacks compatible with CMOS technology. Journal Physics D: Applied Physics, 2021, 54, 225101.	1.3	9
85	Defect Formation during MBE Growth of CdTe (111). Physica Status Solidi A, 1991, 126, 181-188.	1.7	8
86	InP decomposition phosphorus beam source for MBE: design, properties and superlattice growth. Semiconductor Science and Technology, 2003, 18, 417-422.	1.0	8
87	Instability of the distribution of atomic steps on Si(111) upon submonolayer gold adsorption at high temperatures. JETP Letters, 2005, 81, 117-121.	0.4	8
88	Preparation of thin films of platinum group metals by pulsed MOCVD. II. Deposition of Ru layers. Journal of Structural Chemistry, 2012, 53, 725-733.	0.3	8
89	New system of self-assembled GaSb/GaP quantum dots. Semiconductors, 2012, 46, 1534-1538.	0.2	8
90	Coexistence of type-I and type-II band alignment in Ga(Sb, P)/GaP heterostructures with pseudomorphic self-assembled quantum dots. JETP Letters, 2014, 99, 76-81.	0.4	8

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91	Peculiarities of structure, morphology, and electrochemistry of the doped 5-V spinel cathode materials LiNi0.5-x Mn1.5-y M x+y O4 (Mâ€‰=â€‰Co, Cr, Ti; x+yâ€‰=â€‰0.05) prepared by mechanochemical way. Journal of Solid State Electrochemistry, 2016, 20, 235-246.	1.2	8
92	MBE-grown InSb photodetector arrays. Technical Physics, 2017, 62, 915-919.	0.2	8
93	Fluorinated graphene nanoparticles with 1â€“3 nm electrically active graphene quantum dots. Nanotechnology, 2020, 31, 295602.	1.3	8
94	Defects and their Electronic Properties in High-Pressure-Annealed SOI Structures Sliced by Hydrogen. , 2002, , 269-288.		8
95	In Situ HREM Irradiation Study of an Intrinsic Point Defects Clustering in FZ-Si. Crystal Research and Technology, 2000, 35, 775-786.	0.6	7
96	MODIFICATION OF GROWTH MODE OF Ge ON Si BY PULSED LOW-ENERGY ION-BEAM IRRADIATION. International Journal of Nanoscience, 2004, 03, 19-27.	0.4	7
97	Formation of nanocrystalline silicon films using high-dose H+ ion implantation into silicon-on-insulator layers with subsequent rapid thermal annealing. Semiconductors, 2004, 38, 107-112.	0.2	7
98	High-precision nanoscale length measurement. Nanotechnologies in Russia, 2013, 8, 518-531.	0.7	7
99	Dual threshold diode based on the superconductor-to-insulator transition in ultrathin TiN films. Applied Physics Letters, 2013, 102, .	1.5	7
100	Formation of iron and iron silicides on silicon and iron surfaces. Role of the deposition rate and volumetric effects. Applied Physics A: Materials Science and Processing, 2013, 112, 507-515.	1.1	7
101	Ferromagnetic HfO2/Si/GaAs interface for spin-polarimetry applications. Applied Physics Letters, 2015, 107, .	1.5	7
102	Photoluminescence associated with {113} defects in oxygenâ€implanted silicon. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700317.	0.8	7
103	Resistive Switching Effect with ON/OFF Current Relation up to 10⁹ in 2D Printed Composite Films of Fluorinated Graphene with V₂O₅ Nanoparticles. Advanced Electronic Materials, 2019, 5, 1900310.	2.6	7
104	Bimetallic Pt,Ir-containing coatings formed by MOCVD for medical applications. Journal of Materials Science: Materials in Medicine, 2019, 30, 69.	1.7	7
105	Resistive switching on individual V₂O₅nanoparticles encapsulated in fluorinated graphene films. Physical Chemistry Chemical Physics, 2021, 23, 20434-20443.	1.3	7
106	Transformation of the InP(001) surface upon annealing in an arsenic flux. Surface Science, 2021, 710, 121861.	0.8	7
107	Morphological transformations of vanadium oxide films during low-temperature reduction in hydrogen electron cyclotron resonance plasma. Journal of Surface Investigation, 2007, 1, 454-461.	0.1	6
108	Influence of shape of GaN/AlN quantum dots on luminescence decay law. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 653-656.	0.8	6

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109	High-quality single-crystal diamond-graphite-diamond membranes and devices. International Journal of Nanotechnology, 2015, 12, 226.	0.1	6
110	Raman, AFM, and TEM profiling of QD multilayer structures. Materials Research Express, 2015, 2, 035003.	0.8	6
111	Recombination and spin dynamics of excitons in thin (Ga,Al)(Sb,As)/AlAs quantum wells with an indirect band gap and type-I band alignment. Physical Review B, 2020, 102, .	1.1	6
112	Synthesis of crystalline Mg2Si films by ultrafast deposition of Mg on Si(111) and Si(001) at high temperatures. Mg/Si intermixing and reaction mechanisms. Materials Chemistry and Physics, 2021, 258, 123903.	2.0	6
113	Extended Defects in O+-Implanted Si Layers and Their Luminescence. Crystallography Reports, 2021, 66, 625-635.	0.1	6
114	On the mechanism of {113}-defect formation in Si. , 2005, , 359-362.		6
115	Intrinsic Point Defect Clustering in Si: A Study by HVEM and HREM in Situ Electron Irradiation. , 1997, , 63-92.		6
116	Epitaxial silicon films deposited at high rates by gas-jet electron beam plasma CVD. Surface and Coatings Technology, 2003, 174-175, 1178-1181.	2.2	5
117	Formation of Ultrasmall Germanium Nanoislands with a High Density on an Atomically Clean Surface of Silicon Oxide. Physics of the Solid State, 2005, 47, 67.	0.2	5
118	Narrowing of ground energy level distribution in an array of InAs/AlAs QDs by post grown annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3932-3934.	0.8	5
119	Origination of misfit dislocations at the surface during the growth of GeSi/Si(001) films by low-temperature (300â€“400Â°C) molecular-beam epitaxy. Semiconductors, 2006, 40, 319-326.	0.2	5
120	Pulsed ion-beam assisted deposition of Ge nanocrystals on SiO2 for non-volatile memory device. Thin Solid Films, 2008, 517, 313-316.	0.8	5
121	Investigation of Multilayer Silicon Structures with Buried Iron Silicide Nanocrystallites: Growth, Structure, and Properties. Journal of Nanoscience and Nanotechnology, 2008, 8, 527-534.	0.9	5
122	Spontaneous composition modulation during Cd x Hg1â^'x Te(301) molecular beam epitaxy. JETP Letters, 2011, 94, 324-328.	0.4	5
123	Decomposition of a supersaturated solid solution of Fe in GaAs. Inorganic Materials, 2012, 48, 93-95.	0.2	5
124	Structure and Optical Properties of Ca Silicide Films and Si/Ca₃Si₄/Si(111) Heterostructures. Solid State Phenomena, 2014, 213, 71-79.	0.3	5
125	Specific features of plastic relaxation of a metastable Ge x Si1 â^' x layer buried between a silicon substrate and a relaxed germanium layer. Physics of the Solid State, 2014, 56, 247-253.	0.2	5
126	Formation of Mg silicides on amorphous Si. Origin and role of high pressure in the film growth. Materials Chemistry and Physics, 2014, 148, 1078-1082.	2.0	5

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127	Strained multilayer structures with pseudomorphic GeSiSn layers. Semiconductors, 2016, 50, 1584-1588.	0.2	5
128	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). Journal of Crystal Growth, 2017, 457, 215-219.	0.7	5
129	Formation of low-dimensional structures in the InSb/AlAs heterosystem. Semiconductors, 2017, 51, 1233-1239.	0.2	5
130	Spinodal Decomposition in InSb/AlAs Heterostructures. Semiconductors, 2018, 52, 1392-1397.	0.2	5
131	Influence of a Low-Temperature GaAs Dislocation Filter on the Perfection of GaAs/Si Layers. Optoelectronics, Instrumentation and Data Processing, 2018, 54, 181-186.	0.2	5
132	GaAs/GaP Quantum-Well Heterostructures Grown on Si Substrates. Semiconductors, 2019, 53, 1143-1147.	0.2	5
133	Structure of Hf0.9La0.1O2 Ferroelectric Films Obtained by the Atomic Layer Deposition. JETP Letters, 2019, 109, 116-120.	0.4	5
134	Graphene/Hexagonal Boron Nitride Composite Nanoparticles for 2D Printing Technologies. Advanced Engineering Materials, 2022, 24, 2100917.	1.6	5
135	Structure of cadmium and lead sulfide nanoclusters in a matrix of a langmuir-blodgett film. Journal of Structural Chemistry, 1999, 40, 485-487.	0.3	4
136	Defects in silicon heat-treated under uniform stress and irradiated with fast neutrons. Physica Status Solidi A, 2003, 199, 207-213.	1.7	4
137	Formation, crystal structure, and properties of silicon with buried iron disilicide nanocrystallites on Si (100) substrates. Semiconductors, 2007, 41, 1067-1073.	0.2	4
138	Plastic relaxation of GeSi/Si(001) films grown by molecular-beam epitaxy in the presence of the Sb surfactant. Semiconductors, 2007, 41, 1234-1239.	0.2	4
139	Crystal perfection of GaP films grown on Si substrates by solid-source MBE with atomic hydrogen. Semiconductors, 2009, 43, 1235-1239.	0.2	4
140	Strained germanium films in Ge/InGaAs/GaAs heterostructures: Formation of edge misfit dislocations at the Ge/InGaAs interface. Physics of the Solid State, 2011, 53, 2005-2011.	0.2	4
141	Non-linear conduction in the critical region of the superconductor-insulator transition in TiN thin films. Journal of Physics: Conference Series, 2012, 400, 022042.	0.3	4
142	Edge misfit dislocations in the GeSi/Si(001) pair: Conditions and specific features of high-quantity generation. Journal of Crystal Growth, 2012, 338, 12-15.	0.7	4
143	Structural state of Ge/Si heterosystems with (001), (111), and (7 7 10) interfaces. Bulletin of the Russian Academy of Sciences: Physics, 2012, 76, 325-327.	0.1	4
144	Analysis of the dislocation structure at the Ge/Si(111) heterointerface. Journal of Surface Investigation, 2014, 8, 787-793.	0.1	4

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145	InAsSb on GaAs (001): influence of the arsenic molecules form on composition and crystalline properties of MBE layers. Journal of Physics: Conference Series, 2015, 643, 012006.	0.3	4
146	Formation and crystal structure of GaSb/GaP quantum dots. Bulletin of the Russian Academy of Sciences: Physics, 2016, 80, 17-22.	0.1	4
147	Unexpected travel of Lomer-type dislocations in Ge/GexSi1-x/Si(001) heterostructures. Thin Solid Films, 2016, 616, 348-350.	0.8	4
148	Selective MOCVD synthesis of VO₂ crystals on nanosharp Si structures. CrystEngComm, 2021, 23, 443-452.	1.3	4
149	Epitaxial growth of peculiar GeSn and SiSn nanostructures using a Sn island array as a seed. Applied Surface Science, 2021, 553, 149572.	3.1	4
150	The plastic deformation kinetics for heteroepitaxial films during the misfit dislocation generation from the growth surface. Physica Status Solidi A, 1981, 66, 249-253.	1.7	3
151	Self-Orientation of Silicon Nanocrystals Created under Pulse Laser Impact in Stressed Î±-Si:H Films on Glass Substrates. Solid State Phenomena, 2001, 82-84, 681-686.	0.3	3
152	Influence of the misfit-dislocation screw component on the formation of threading dislocations in semiconductor heterostructures. Semiconductors, 2002, 36, 290-297.	0.2	3
153	Ge Nanoclusters in GeO₂: Synthesis and Optical Properties. Solid State Phenomena, 2005, 108-109, 83-90.	0.3	3
154	<title>Dense arrays of Ge nanoclusters induced by low-energy ion-beam assisted deposition on Si0<formula><inf><roman>2</roman></inf></formula> films</title>. , 2006, , .		3
155	Role of the dislocation screw component in the formation of the dislocation structure in Ge- and Si-based semiconductor heterosystems. Journal of Surface Investigation, 2007, 1, 247-254.	0.1	3
156	Silicon layers atop iron silicide nanoislands on Si(100) substrate: Island formation, silicon growth, morphology and structure. Thin Solid Films, 2007, 515, 7805-7812.	0.8	3
157	Effect of the ion-energy loss rate on defect formation during implantation in silicon nanocrystals. Semiconductors, 2008, 42, 1127-1131.	0.2	3
158	Formation of misfit edge dislocations in Ge x Si1 â^' x films (x â^¼ 0.4â€“0.5) grown on tilted Si(001) â†' (111) substrates. Physics of the Solid State, 2008, 50, 1857-1861.	0.2	3
159	Heteroepitaxy of Ge x Si1 â^' x (x â^¼ 0.4â€“0.5) films on Si(001) substrates misoriented to (111): Formation of short edge misfit dislocations alone in the misorientation direction. Physics of the Solid State, 2010, 52, 32-36.	0.2	3
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161	Optical property improvement of InAs/GaAs quantum dots grown by hydrogen-plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	3
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